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PATENT APPLICATION  
ATTORNEY DOCKET NO. LMRX-P019/P1154

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Lee et al.  
Application No. 10/623,016  
Filed: 7/17/2003  
Title: TREATMENT FOR CORROSION IN  
SUBSTRATE PROCESSING

Examiner: DEO, Duy V. Nguyen  
Group No. 1765

Confirmation No. 4601

**CERTIFICATE OF FACSIMILE TRANSMISSION**

I hereby certify that this correspondence is being transmitted to the US  
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Signed: /Alma Fazlic/  
Alma Fazlic

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449 may be material to the patentability of the above-identified patent application. Applicants submit the list of these references in compliance with their duty of disclosure pursuant to 37 CFR §§ 1.56 and 1.97. The Examiner is requested to make these references of official record in this application. The above-identified application is a continuation-in-part of prior application U.S. Patent Application No. 10/199,190 filed on July 19, 2002, which in turn is a continuation-in-part of U.S. Patent Application No. 9/820,696 filed on March 30, 2001. This prior application is being relied upon for an earlier filing date under 35 U.S.C. § 120. Because the listed references were either cited by the PTO, or submitted to the PTO in the prior application, under 37 CFR § 1.98(d) Applicants submit that copies need not be provided.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is believed to be filed before the mailing date of a first Office Action on the merits. If it is determined that fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 50-2284 (Order No. LMRX-P019).

Respectfully submitted,

By: /Joseph Nguyen/  
Joseph Nguyen  
Reg. No. 37,899

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## INFORMATION DISCLOSURE STATEMENT

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Examiner Signature		Date Considered	
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